

**ABSTRACT OF THE DISCLOSURE**

A method for etching a tungsten-containing layer (525) on a substrate (510) substantially anisotropically, with good etching selectivity with respect to a hard mask layer, and without forming excessive passivating deposits on the etched features. In the method, the substrate (510) is placed in a plasma zone, and process gas mix comprising  $\text{NF}_3$  and  $\text{Cl}_2$  is introduced into the plasma zone. A plasma is formed from the process gas mix to anisotropically etch the tungsten containing layer (525) to produce patterned tungsten features (535).

525  
510  
535